

SOT-23



Pin Definition:

1. Base
2. Emitter
3. Collector

PRODUCT SUMMARY

BV_{CEO}	40V
BV_{CBO}	75V
I_C	600mA
V_{CE(SAT)}	0.5V @ I _C / I _B = 380mA / 10mA

Features

- Driver Stage of AF Amplifier
- General Purpose Switching Application

Structure

- Epitaxial Planar Type
- Complementary to TSA1036CX

Ordering Information

Part No.	Package	Packing
TSC2411CX RF	SOT-23	3Kpcs / 7" Reel

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Collector-Base Voltage	V _{CBO}	75	V
Collector-Emitter Voltage	V _{CEO}	40	V
Emitter-Base Voltage	V _{EBO}	6	V
Collector Current	I _C	600	mA
Collector Power Dissipation	P _D	225	mW
Operating Junction Temperature	T _J	+150	°C
Operating Junction and Storage Temperature Range	T _{STG}	- 55 to +150	°C

Note: 1. Single pulse, Pw=20ms, Duty≤50%

2. When mounted on a 40 x 50 x 0.7mm ceramic board.

Electrical Specifications (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	I _C = 10uA, I _E = 0	BV _{CBO}	75	--	--	V
Collector-Emitter Breakdown Voltage	I _C = 10mA, I _B = 0	BV _{CEO}	40	--	--	V
Emitter-Base Breakdown Voltage	I _E = 10uA, I _C = 0	BV _{EBO}	6	--	--	V
Collector Cutoff Current	V _{CB} = 60V, I _E = 0	I _{CBO}	--	--	0.1	uA
Emitter Cutoff Current	V _{EB} = 3V, I _C = 0	I _{EBO}	--	--	0.1	uA
Collector-Emitter Saturation Voltage	I _C / I _B = 380mA / 10mA	V _{CE(SAT)} 1	--	0.2	0.5	V
Collector-Emitter Saturation Voltage	I _C / I _B = 150mA / 15mA	V _{CE(SAT)} 2	--	0.2	0.4	V
Collector-Emitter Saturation Voltage	I _C / I _B = 500mA / 50mA	V _{CE(SAT)} 3	--	0.45	0.75	V
Base-Emitter Saturation Voltage	I _C / I _B = 150mA / 15mA	V _{BE(SAT)} 1	0.75	--	0.95	V
Base-Emitter Saturation Voltage	I _C / I _B = 500mA / 50mA	V _{BE(SAT)} 2	--	--	1.2	V
DC Current Transfer Ratio	V _{CE} = 1V, I _C = 150mA	h _{FE}	82	--	390	
Transition Frequency	V _{CE} = 5V, I _C = 20mA, f = 100MHz	f _T	300	--	--	MHz
Output Capacitance	V _{CB} = 5V, f = 1MHz	Cob	--	6	--	pF

Electrical Characteristics Curve ($T_a = 25^\circ\text{C}$, unless otherwise noted)

Figure 1. DC Current Gain

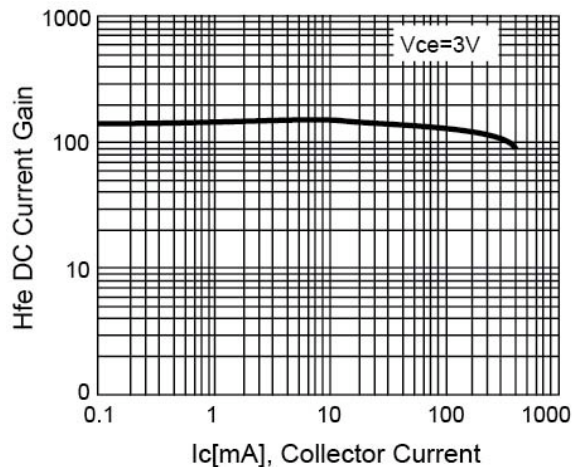


Figure 2. $V_{ce(sat)}$ v.s. I_c

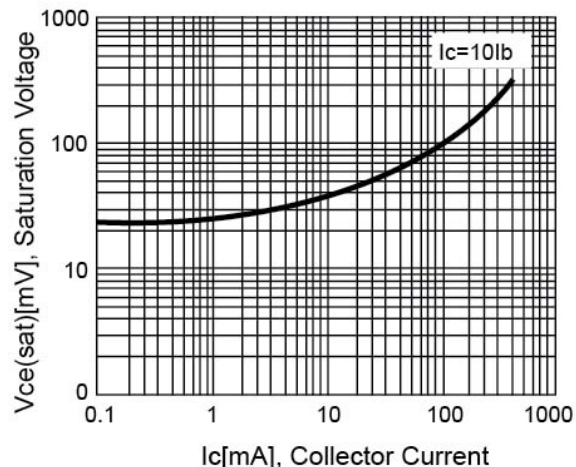


Figure 3. $V_{be(sat)}$ v.s. I_c

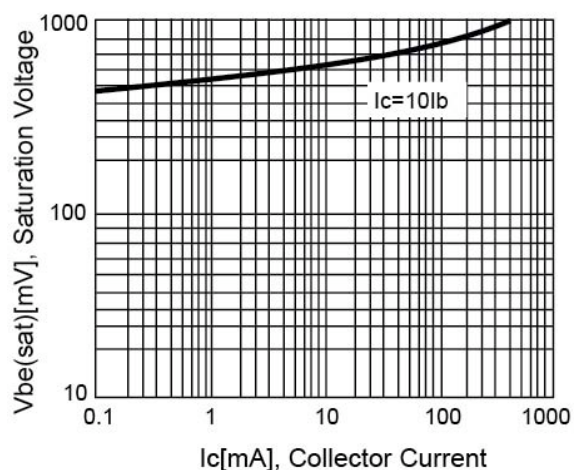


Figure 4. Cutoff Frequency vs. I_c

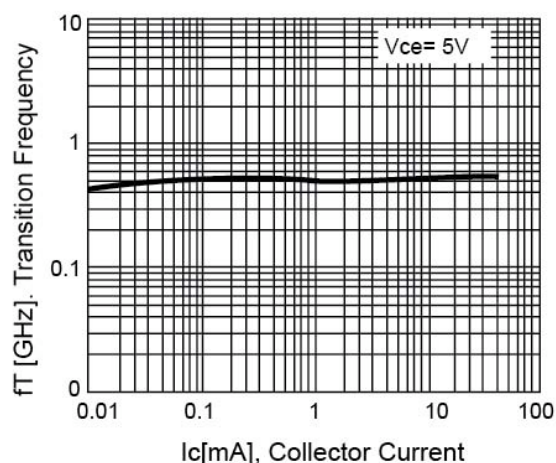
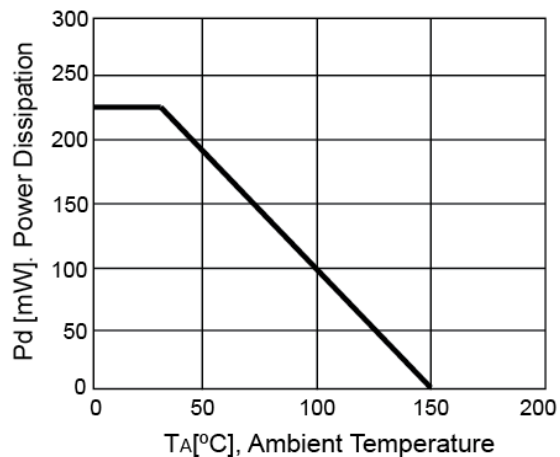
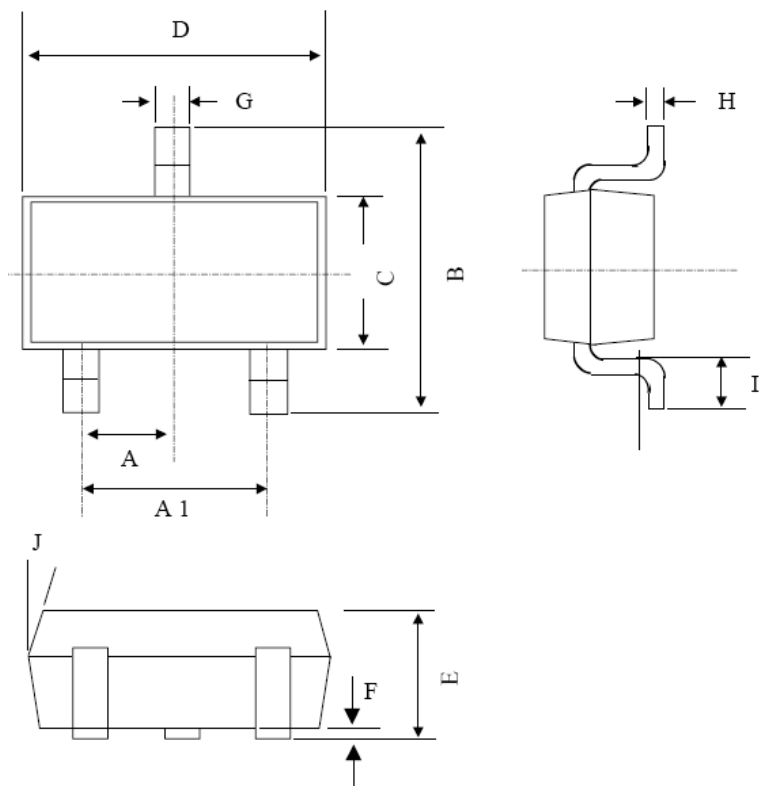


Figure 5. Power Derating Curve



SOT-23 Mechanical Drawing



DIM	SOT-23 DIMENSION			
	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX.
A	0.95 BSC		0.037 BSC	
A1	1.9 BSC		0.074 BSC	
B	2.60	3.00	0.102	0.118
C	1.40	1.70	0.055	0.067
D	2.80	3.10	0.110	0.122
E	1.00	1.30	0.039	0.051
F	0.00	0.10	0.000	0.004
G	0.35	0.50	0.014	0.020
H	0.10	0.20	0.004	0.008
I	0.30	0.60	0.012	0.024
J	5°	10°	5°	10°

TSC2411

General Purpose NPN Transistor

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